

<p>Substitute for form 1449A/PTO</p> <h1 style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h1> <p><i>(use as many sheets as necessary)</i></p>				<b>C omplete if Known</b>	
Sheet	1	of	1	Application Number	10/730,855
				Filing Date	12/08/03
				First Named Inventor	Soon-Yong Kweon
				Art Unit	2811
				Examiner Name	HUNG VU
				Attorney Docket Number	51876P422

## **NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T3
<u>Va</u>		KR Laid-Open No. 2003-23844	
<u>Va</u>		0.18 $\mu$ m SBT-Based Embedded FeRAM Operating at a Low Voltage of 1.1V (2003 Symposium on VLSI Technology Digest of Technical Papers)	
<u>Va</u>		Highly Manufacturable and Reliable 32 Mb FRAM Technology with Novel BC and Capacitor Cleaning Process (2003 Symposium on VLSI Technology Digest of Technical Papers)	

Examiner Signature	HUNG VU	Date Considered	6/17/04
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*\*Examiner: initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.*

<sup>1</sup>Applicant's unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08B (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wtr) 08/11/2003.  
Send To: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450